



# WBFBP-03B Plastic-Encapsulate Transistors

## MMBT3904M TRANSISTOR

### DESCRIPTION

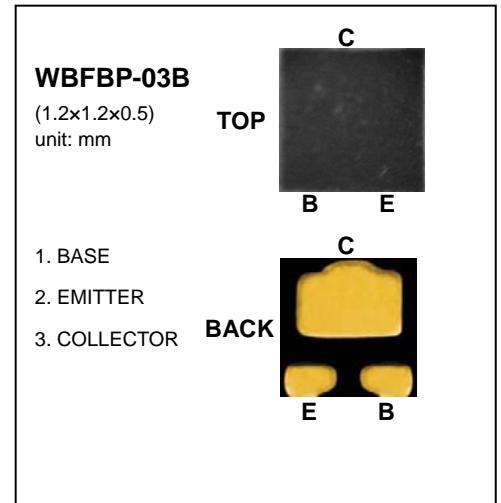
NPN Epitaxial Silicon Transistor

### FEATURES

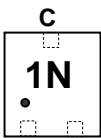
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT3906M)
- Ultra-Small Surface Mount Package
- Also Available in Lead Free Version

### APPLICATION

General Purpose Amplifier, switching  
 For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



### MARKING:1N



### MAXIMUM RATINGS\* T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current -Continuous	0.2	A
P <sub>C</sub>	Collector Dissipation	0.15	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)

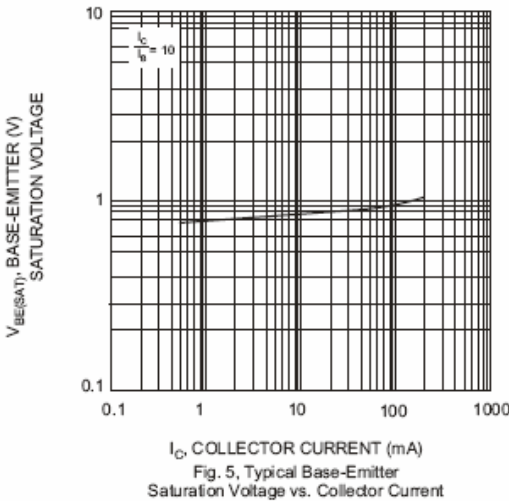
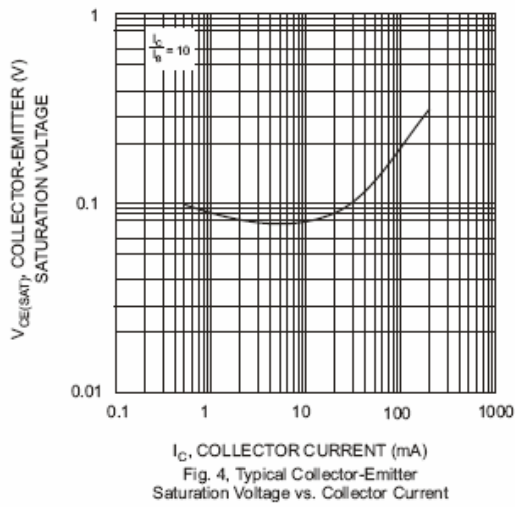
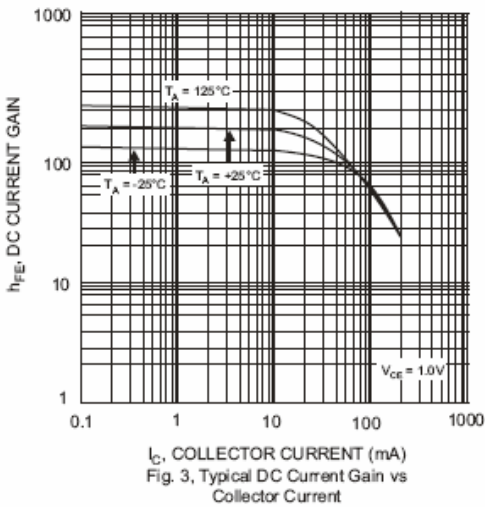
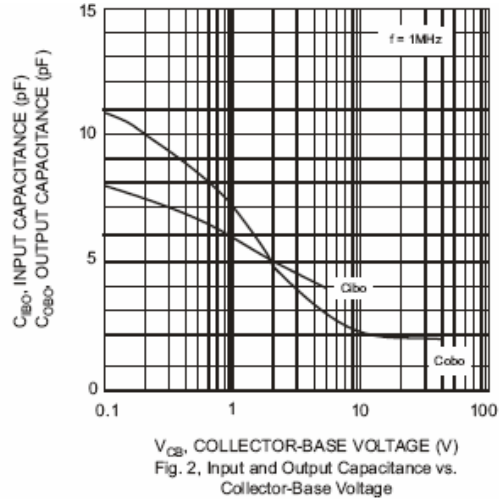
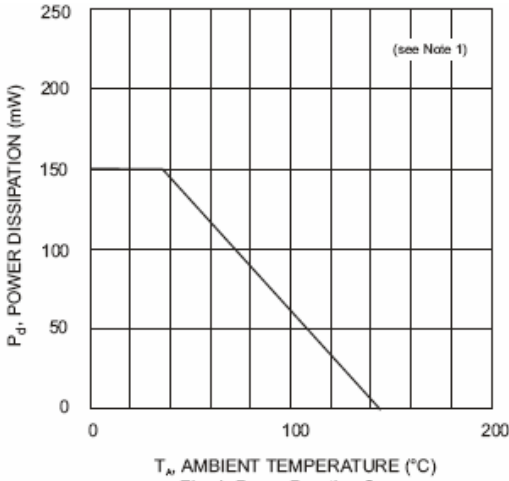
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =30V, V <sub>EB(off)</sub> =3V			0.05	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =0.1mA	40			
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =1mA	70			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA	100		300	
	h <sub>FE(4)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =50mA	60			
	h <sub>FE(5)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.2	V
	V <sub>CE(sat)2</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)1</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA	0.65		0.85	V
	V <sub>BE(sat)2</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.95	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=100MHz	300			MHz

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

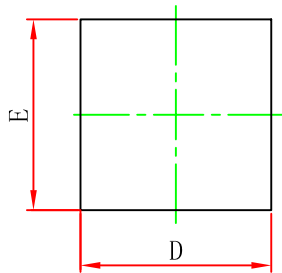
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz			4	pF
Noise figure	NF	V <sub>CE</sub> =5V, I <sub>c</sub> =0.1mA,			5	dB
Delay time	t <sub>d</sub>	V <sub>CC</sub> =3V, V <sub>BE (off)</sub> = -0.5V,			35	nS
Rise time	t <sub>r</sub>	I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA			35	nS
Storage time	t <sub>S</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA			200	nS
Fall time	t <sub>f</sub>	I <sub>B1</sub> = I <sub>B2</sub> = 1mA			50	nS

**Typical Characteristics**

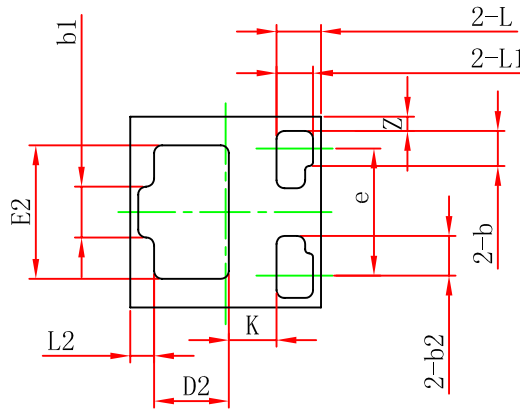
**MMBT3904M**



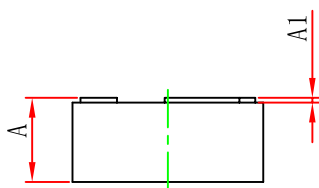
# WBFBP-03B(1.2×1.2×0.5) PACKAGE OUTLINE DIMENSIONS



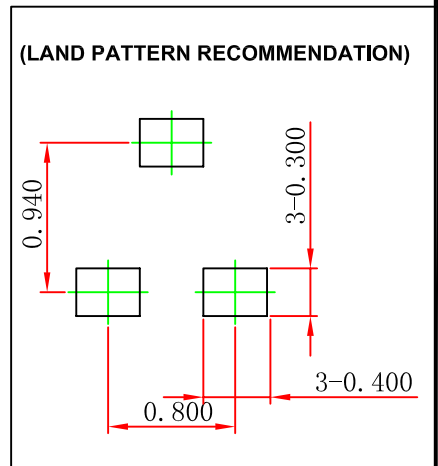
TOP VIEW



BOTTOM VIEW



SIDE VIEW



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.090	0.000	0.004
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
b2	0.250 REF.		0.010 REF.	
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
D2	0.470 REF.		0.002 REF.	
E2	0.810 REF.		0.032 REF.	
e	0.800 TYP.		0.032 TYP.	
L	0.280 REF.		0.011 REF.	
L1	0.230 REF.		0.009 REF.	
L2	0.150 REF.		0.006 REF.	
k	0.300 REF.		0.012 REF.	
z	0.090 REF.		0.004 REF.	